



## AO4800B, AO4800BL

### Dual N-Channel Enhancement Mode Field Effect Transistor

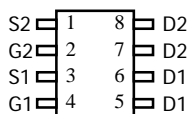
#### General Description

The AO4800B/L uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. The two MOSFETs make a compact and efficient switch and synchronous rectifier combination for use in buck converters. *Standard Product AO4800B/L is Pb-free (meets ROHS & Sony 259 specifications).*

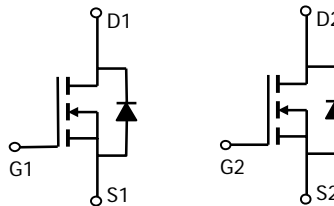
#### Features

$V_{DS} (V) = 30V$   
 $I_D = 6.9A (V_{GS} = 10V)$   
 $R_{DS(ON)} < 27m\Omega (V_{GS} = 10V)$   
 $R_{DS(ON)} < 32m\Omega (V_{GS} = 4.5V)$   
 $R_{DS(ON)} < 50m\Omega (V_{GS} = 2.5V)$

**UIS TESTED!**  
**Rg, Ciss, Coss, Crss Tested!**



SOIC-8



#### Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current <sup>AF</sup>	$I_D$	$T_A=25^\circ C$	A
		$T_A=70^\circ C$	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	40	
Power Dissipation	$P_D$	$T_A=25^\circ C$	W
		$T_A=70^\circ C$	
Avalanche Current <sup>B</sup>	$I_{AR}$	12	A
Repetitive avalanche energy 0.3mH <sup>B</sup>	$E_{AR}$	22	mJ
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ C$

#### Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>AF</sup>	$R_{\theta JA}$	55	62.5	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>		Steady-State	90	110
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	40	48	$^\circ C/W$

Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C		0.002	1 5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±12V			100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.7	1	1.5	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =5V	40			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =6.9A T <sub>J</sub> =125°C		20 25	27 40	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A		23	32	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =5A		34	50	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =5A	10	26		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.71	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				4.5	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz		900	1100	pF
C <sub>oss</sub>	Output Capacitance			88		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			65		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		0.95	1.5	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =15V, I <sub>D</sub> =8.5A		10	12	nC
Q <sub>gs</sub>	Gate Source Charge			1.8		nC
Q <sub>gd</sub>	Gate Drain Charge			3.75		nC
t <sub>D(on)</sub>	Turn-On Delay Time	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =1.8Ω, R <sub>GEN</sub> =6Ω		3.2		ns
t <sub>r</sub>	Turn-On Rise Time			3.5		ns
t <sub>D(off)</sub>	Turn-Off Delay Time			21.5		ns
t <sub>f</sub>	Turn-Off Fall Time			2.7		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =5A, di/dt=100A/μs		16.8	20	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =5A, di/dt=100A/μs		8	12	nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t<sub>s</sub> ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

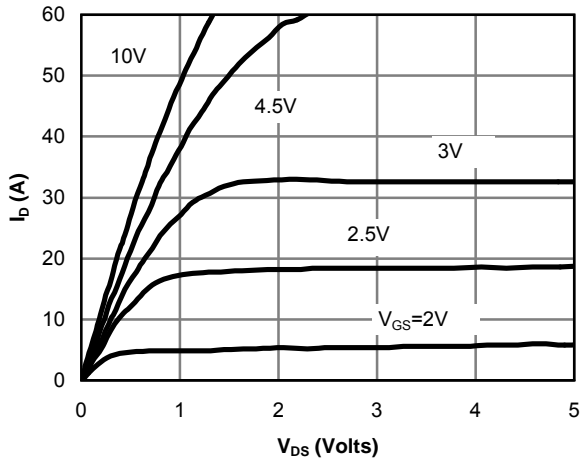


Fig 1: On-Region Characteristics

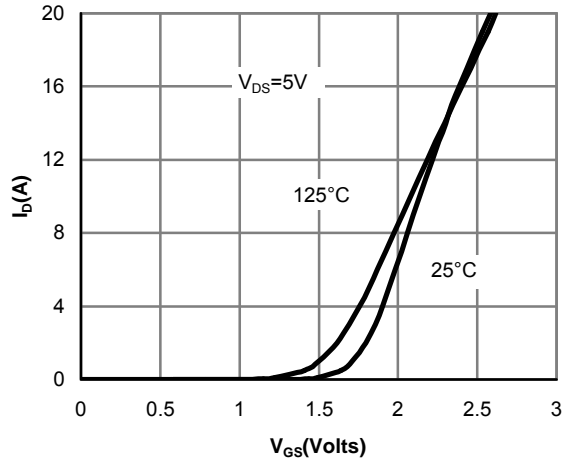


Figure 2: Transfer Characteristics

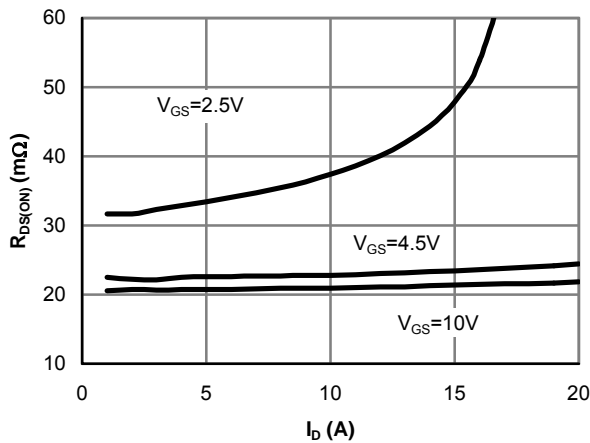


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

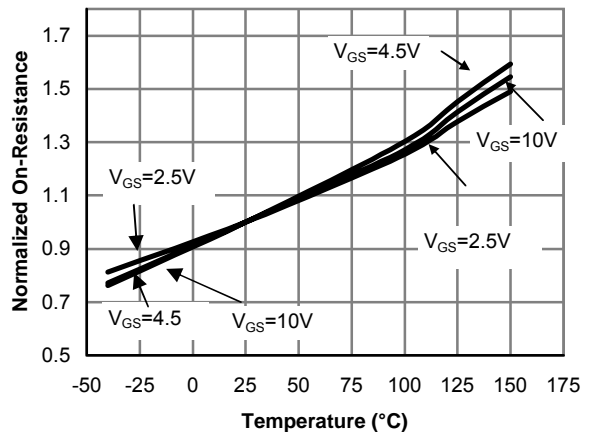


Figure 4: On-Resistance vs. Junction Temperature

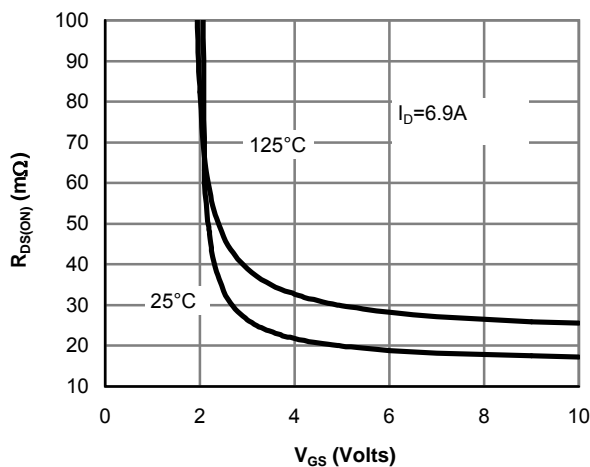


Figure 5: On-Resistance vs. Gate-Source Voltage

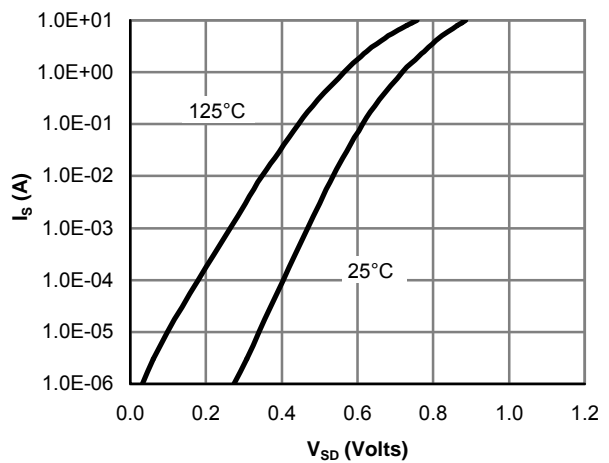


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

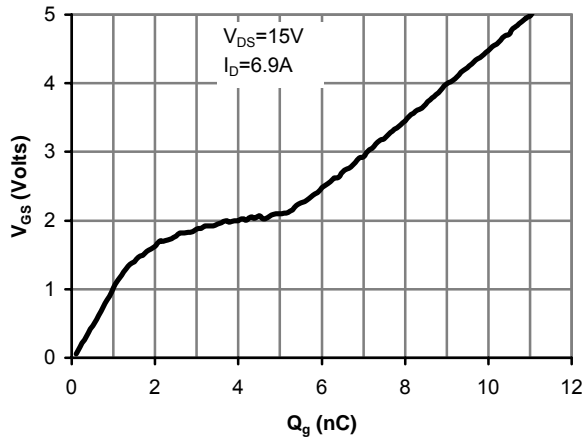


Figure 7: Gate-Charge Characteristics

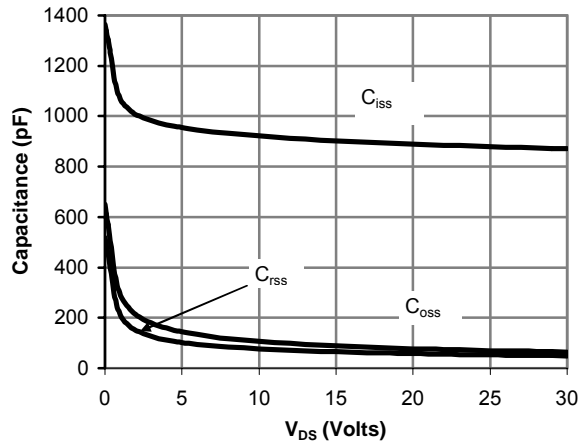


Figure 8: Capacitance Characteristics

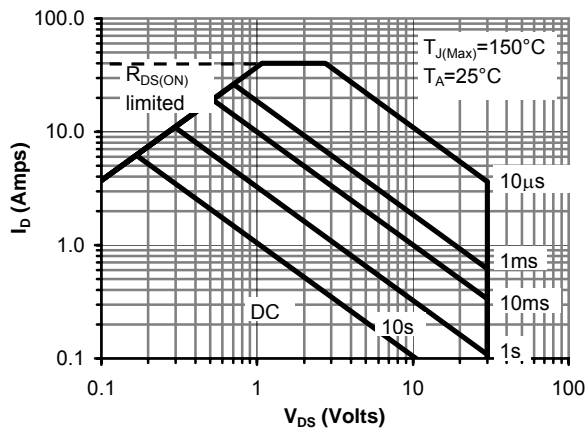


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

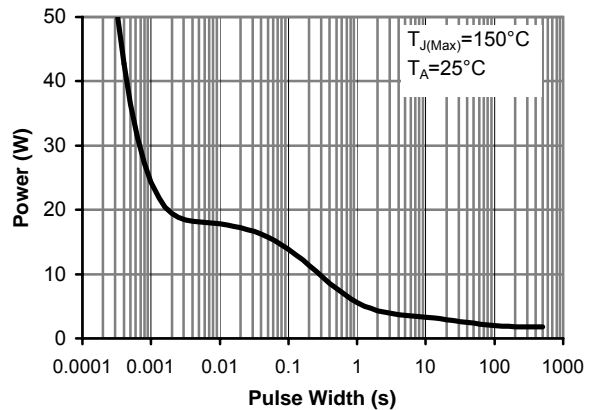


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

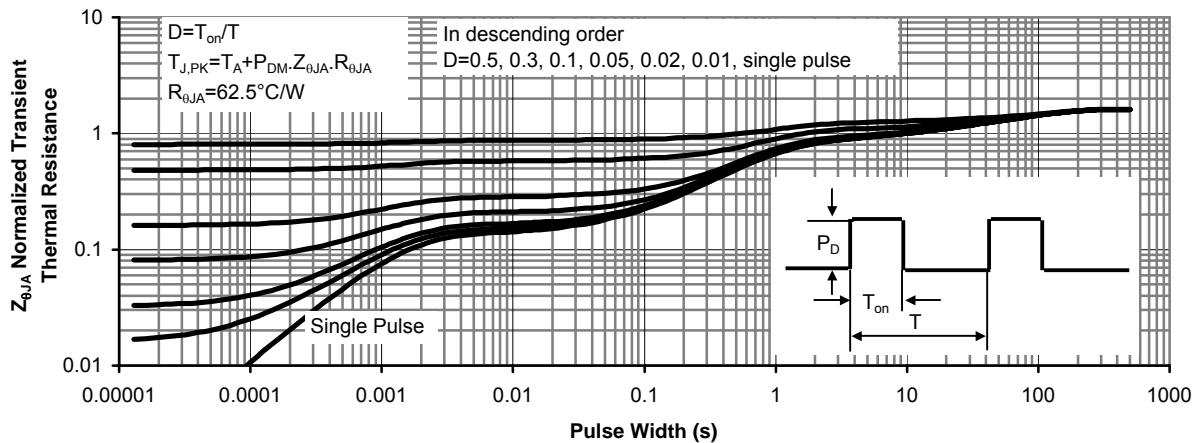


Figure 11: Normalized Maximum Transient Thermal Impedance